

140 COMMERCE DRIVE MONTGOMERYVILLE, PA 18936-1013

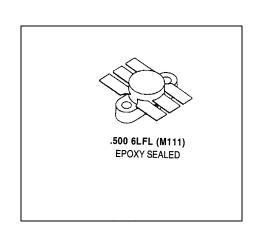
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### MS1527

# RF & MICROWAVE TRANSISTORS UHF COMMUNICATIONS APPLICATIONS

#### **Features**

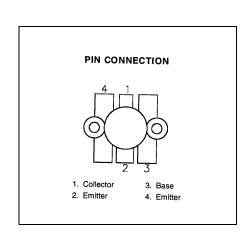
- 400 MHz
- 28 VOLTS
- P<sub>OUT</sub> = 25 WATTS
- G<sub>P</sub> = 9 dB GAIN MINIMUM
- EMITTER BALLASTED
- METAL/CERAMIC PACKAGE
- INTERNAL INPUT MATCHING
- REFRACTORY/GOLD METALIZATION



### **DESCRIPTION:**

The MS1527 is a gold metallized epitaxial silicon NPN planar transistor using diffused emitter ballast resistors for superior ruggedness.

The MS1527 can withstand 20:1 VSWR under rated operating conditions and is internally input matched to optimize power gain and efficiency over the band.



### **ABSOLUTE MAXIMUM RATINGS (Tcase = 25°C)**

| Symbol            | Parameter                 | Value    | Unit |
|-------------------|---------------------------|----------|------|
| $V_{CBO}$         | Collector-Base Voltage    | 60       | V    |
| V <sub>CEO</sub>  | Collector-Emitter Voltage | 30       | V    |
| V <sub>EBO</sub>  | Emitter-Base Voltage      | 3.5      | V    |
| Ic                | Device Current            | 3.0      | Α    |
| P <sub>DISS</sub> | Power Dissipation         | 70       | W    |
| Τ <sub>J</sub>    | Junction Temperature      | +200     | °C   |
| T <sub>STG</sub>  | Storage Temperature       | -65 +150 | °C   |

### **Thermal Data**

| R <sub>TH(J-C)</sub> | Thermal Resistance Junction-case | 2.5 | °C/W |  |
|----------------------|----------------------------------|-----|------|--|





## **ELECTRICAL SPECIFICATIONS (Tcase = 25°C)**

## **STATIC**

| Symbol            |                        | Test Conditions      |      | Value |      |      |
|-------------------|------------------------|----------------------|------|-------|------|------|
|                   |                        |                      | Min. | Тур.  | Max. | Unit |
| BV <sub>CBO</sub> | $I_C = 50 \text{ mA}$  | $I_E = 0mA$          | 60   |       |      | V    |
| BV <sub>EBO</sub> | $I_E = 5 \text{ mA}$   | $I_C = 0 \text{ mA}$ | 3.5  |       |      | V    |
| BV <sub>CES</sub> | $I_C = 50 \text{ mA}$  | $V_{BE} = 0 V$       | 60   |       |      | V    |
| I <sub>CBO</sub>  | V <sub>CB</sub> = 30 V | $I_E = 0 \text{ mA}$ |      |       | 3.0  | mA   |
| HFE               | V <sub>CE</sub> = 5 V  | $I_C = 500 A$        | 10   |       | 120  |      |

### **DYNAMIC**

| Symbol           | Test Conditions |                         |      | Value |      |      |
|------------------|-----------------|-------------------------|------|-------|------|------|
|                  |                 |                         | Min. | Typ.  | Max. | Unit |
| P <sub>out</sub> | f = 400 MHz     | $V_{CC} = 28 \text{ V}$ | 25   |       |      | W    |
| ης               | f = 400 MHz     | V <sub>CC</sub> = 28 V  | 50   |       |      | %    |
| G <sub>P</sub>   | f = 400 MHz     | V <sub>CC</sub> = 28 V  | 9.0  |       |      | dB   |
| VSWR             | f = 400 MHz     | V <sub>CC</sub> = 28 V  | 20:1 |       |      |      |
| Сов              | f = 1 MHz       | V <sub>CB</sub> = 28V   |      |       | 30   | pF   |

### **IMPEDANCE DATA**

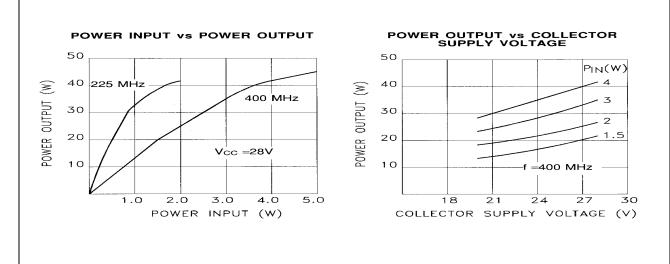
| FREQ    | $Z_IN(\Omega)$ | $Z_{CL}(\Omega)$ |  |
|---------|----------------|------------------|--|
| 225 MHz | 1.40 + j 2.5   | 7.55 + j 0.0     |  |
| 275 MHz | 1.25 + j 3.3   | 7.5 - j 0.05     |  |
| 300 MHz | 1.10 + j 4.0   | 7.5 - j 1.00     |  |
| 350 MHz | 1.10 + j 4.7   | 6.8 - j 1.15     |  |
| 400 MHz | 1.70 + j 5.1   | 6.0 - j 1.30     |  |

 $P_{OUT} = 25 W$  $V_{CE} = 28 V$ 





## **TYPICAL PERFORMANCE**







### PACKAGE MECHANICAL DATA

